

DATA SHEET

MZ0912B50Y

NPN microwave power transistor

Product specification
Supersedes data of November 1994

1997 Feb 18

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FEATURES

- Interdigitated structure provides high emitter efficiency
- Diffused emitter ballasting resistors providing excellent current sharing and withstanding a high VSWR
- Gold metallization realizes very stable characteristics and excellent lifetime
- Multicell geometry gives good balance of dissipated power and low thermal resistance
- Input and output matching cell allows an easier design of circuits.

APPLICATIONS

Common base, class C, broadband, pulse power amplifier from 960 to 1215 MHz for TACAN application.

DESCRIPTION

NPN silicon planar epitaxial microwave power transistor in a SOT443A metal ceramic flange package with base connected to flange. It is mounted in common base configuration, and specified in class C.

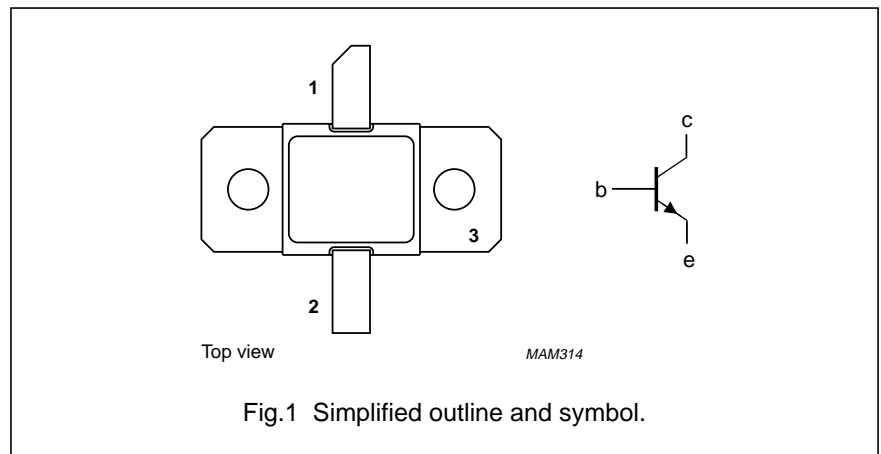
QUICK REFERENCE DATA

Microwave performance up to $T_{mb} = 25\text{ }^{\circ}\text{C}$ in a common base class C broadband amplifier.

MODE OF OPERATION	f (GHz)	V _{CC} (V)	P _L (W)	G _p (dB)	η _c (%)	Z _i /Z _L (Ω)
Class C; t _p = 10 μs; δ = 1%	0.960 to 1.215	50	>50	>7	>42	see Figs 6 and 7

PINNING - SOT443A

PIN	DESCRIPTION
1	collector
2	emitter
3	base connected to flange



WARNING

Product and environmental safety - toxic materials

This product contains beryllium oxide. The product is entirely safe provided that the BeO slab is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

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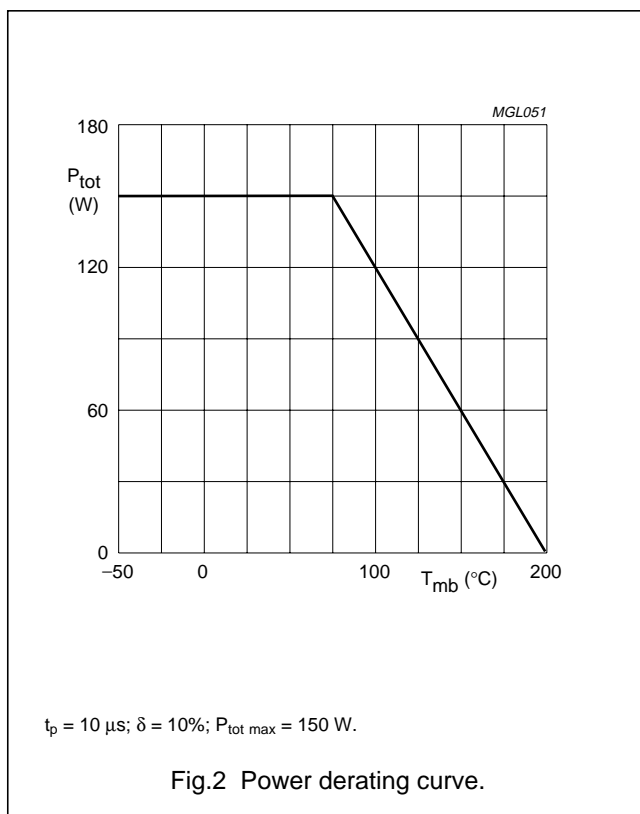
LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	65	V
V_{CEO}	collector-emitter voltage	open base	–	20	V
V_{CES}	collector-emitter voltage	$R_{BE} = 0 \Omega$	–	60	V
V_{EBO}	emitter-base voltage	open collector	–	3	V
I_C	collector current (DC)	$t_p \leq 10 \mu s; \delta \leq 10\%$	–	3	A
P_{tot}	total power dissipation (peak power)	$T_{mb} = 75 \text{ }^\circ\text{C}; t_p \leq 10 \mu s; \delta \leq 10\%$	–	150	W
T_{stg}	storage temperature		–65	+200	$^\circ\text{C}$
T_j	operating junction temperature		–	200	$^\circ\text{C}$
T_{sld}	soldering temperature	$t \leq 10 \text{ s}; \text{note 1}$	–	235	$^\circ\text{C}$

Note

- Up to 0.2 mm from ceramic.



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THERMAL CHARACTERISTICS $T_j = 125\text{ }^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
$R_{th\ j-mb}$	thermal resistance from junction to mounting base	CW	4.9	K/W
$R_{th\ mb-h}$	thermal resistance from mounting base to heatsink	CW; note 1	0.2	K/W
$Z_{th\ j-h}$	thermal impedance from junction to heatsink	notes 1 and 2	0.85	K/W

Notes

- See "Mounting recommendations in the General part of handbook SC19a".
- Equivalent thermal impedance under nominal pulse microwave operating conditions; $t_p = 10\ \mu\text{s}$; $\delta = 10\%$.

CHARACTERISTICS $T_{mb} = 25\text{ }^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
I_{CBO}	collector cut-off current	$V_{CB} = 65\text{ V}; I_E = 0$	20	mA
		$V_{CB} = 50\text{ V}; I_E = 0$	2	mA
I_{CES}	collector cut-off current	$V_{CE} = 60\text{ V}; R_{BE} = 0\ \Omega$	20	mA
I_{EBO}	emitter cut-off current	$V_{EB} = 1.5\text{ V}; I_C = 0$	200	μA

APPLICATION INFORMATION

Microwave performance up to $T_{mb} = 25\text{ }^\circ\text{C}$ measured in the test jig as shown in Fig.3 and working in class C broadband mode in pulse; note 1.

MODE OF OPERATION	f (GHz)	V_{CC} (V) ⁽²⁾	P_L (W)	G_p (dB)	η_c (%)	Z_i/Z_L (Ω)
Class C; $t_p = 10\ \mu\text{s}$; $\delta = 10\%$	0.960 to 1.215	50	>50 typ. 60	>7 typ. 8	>42 typ. 44	see Figs 6 and 7

Notes

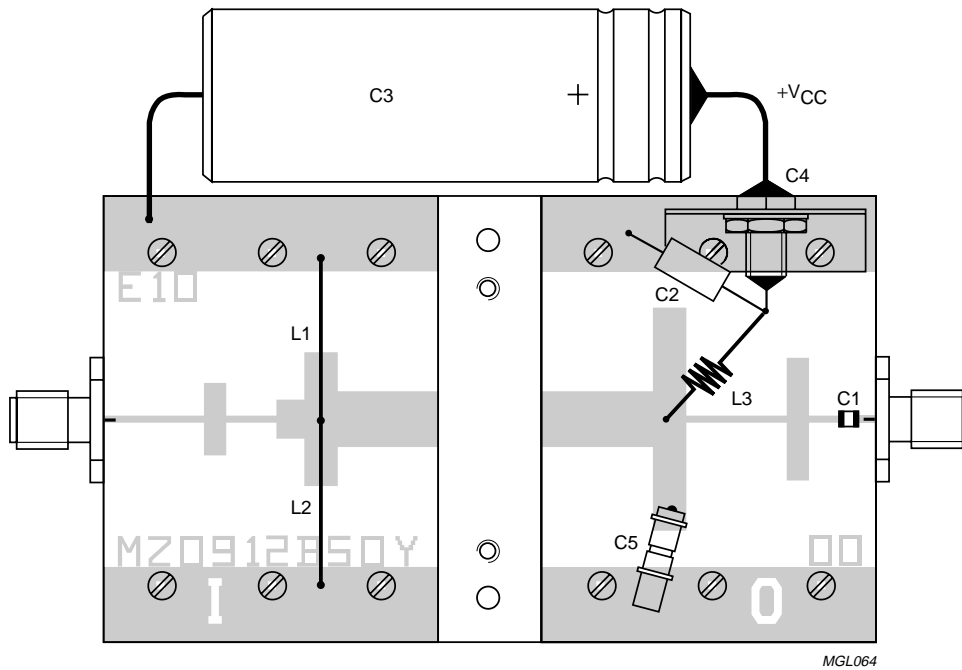
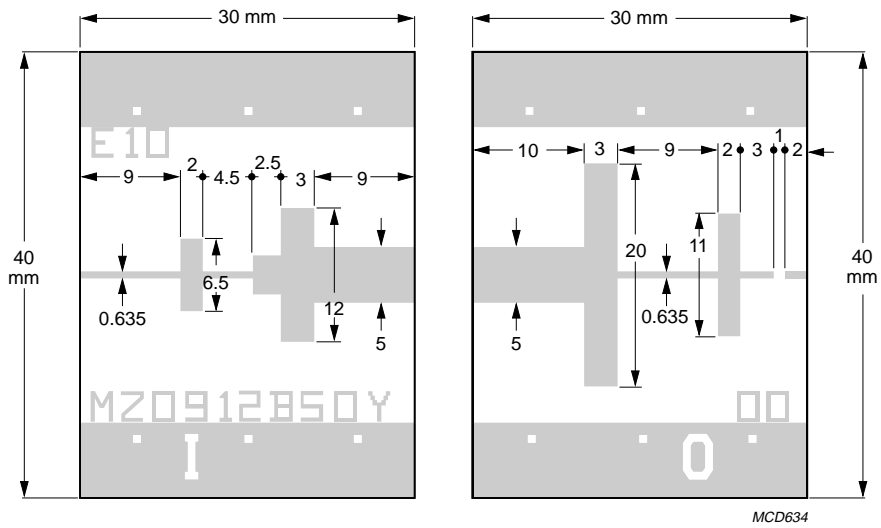
- Operating conditions and performance for other pulse formats can be made available on request.
- V_{CC} during pulse.

List of components (see Fig.3).

COMPONENT	DESCRIPTION	VALUE	DIMENSIONS	CATALOGUE NO.
L1, L2	0.65 mm diameter copper wire	–	total length = 12 mm; height of loop = 9 mm	–
L3	4 turns 0.65 mm diameter copper wire;	–	int. dia. 3 mm; $l = 5\text{ mm}$	–
C1	capacitor	100 pF	–	ATC, ref. 100A101KP50X
C2	tantalum capacitor	10 μF ; 50 V	–	–
C3	electrolytic capacitor	470 μF ; 63 V	–	–
C4	feedthrough bypass capacitor	–	–	Erie, ref. 1250-003
C5, C6	variable gigatrim capacitor	0.6 to 4.5 pF	–	Tekelec, ref. 727.1

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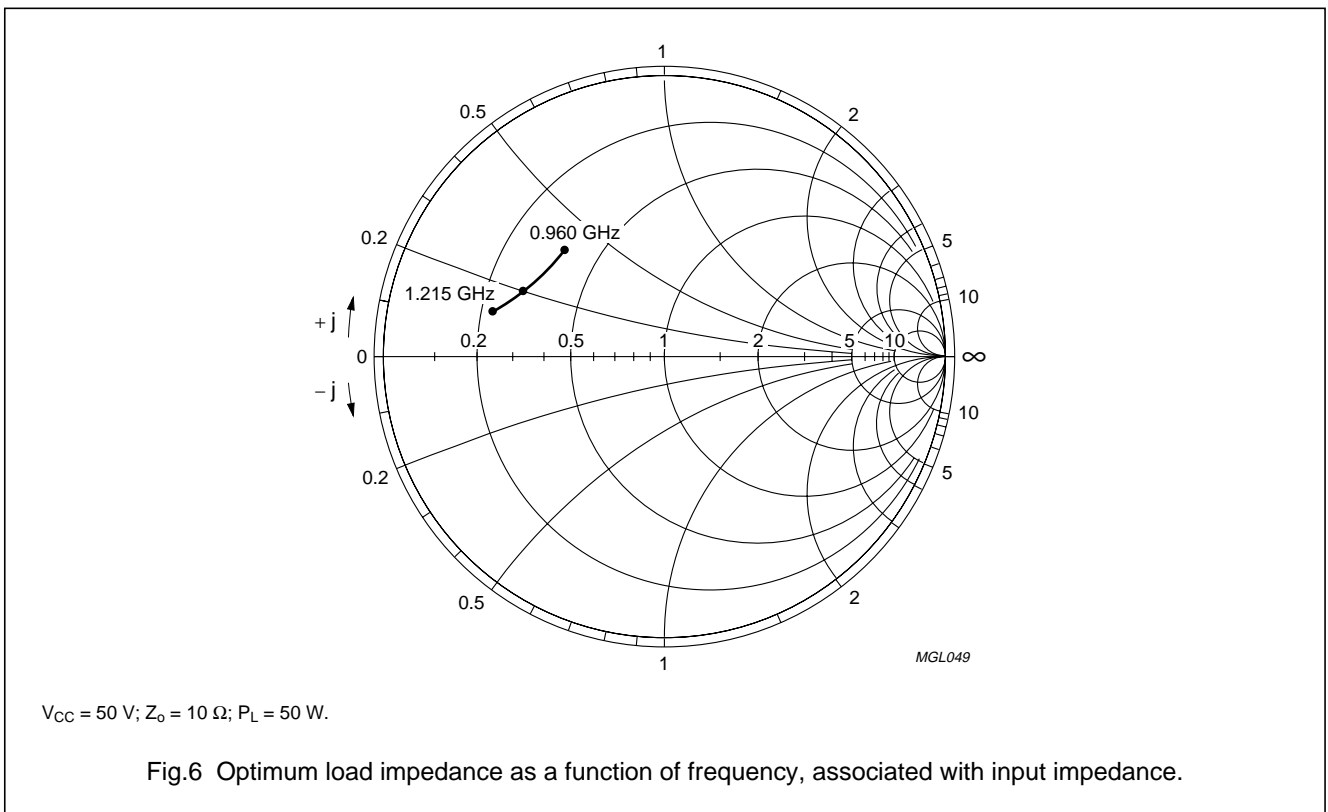
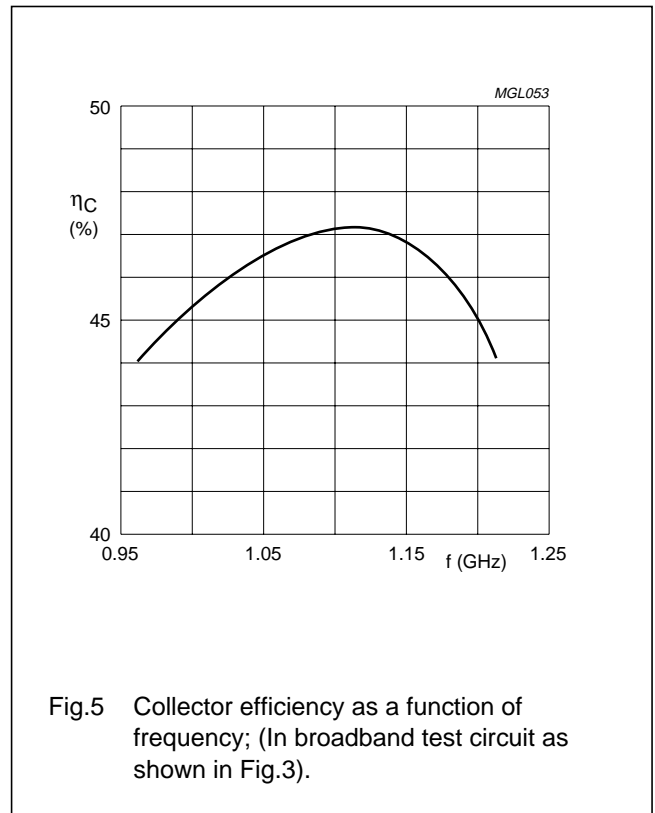
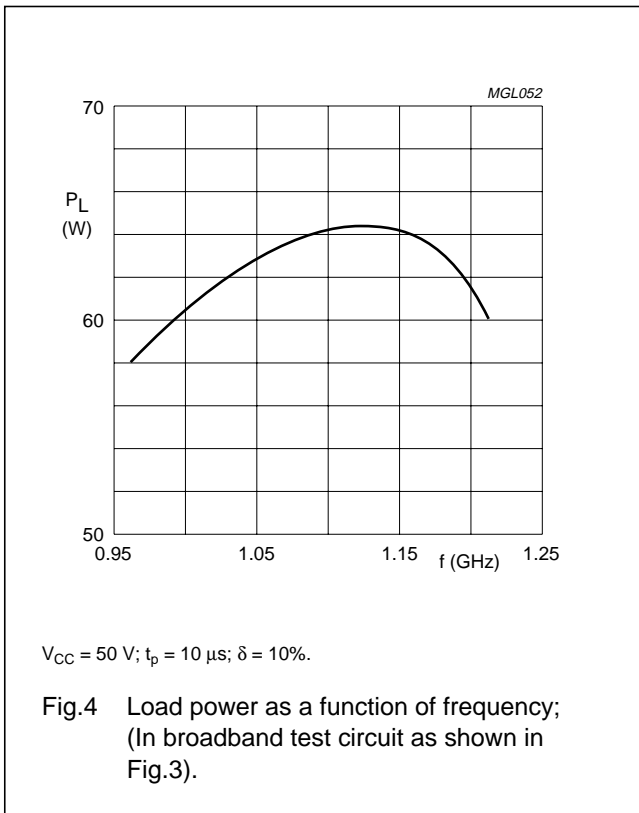


Substrate: Epsilam 10.
 Thickness: 0.635 mm.
 Permittivity: $\epsilon_r = 10$.

Fig.3 Broadband test circuit.

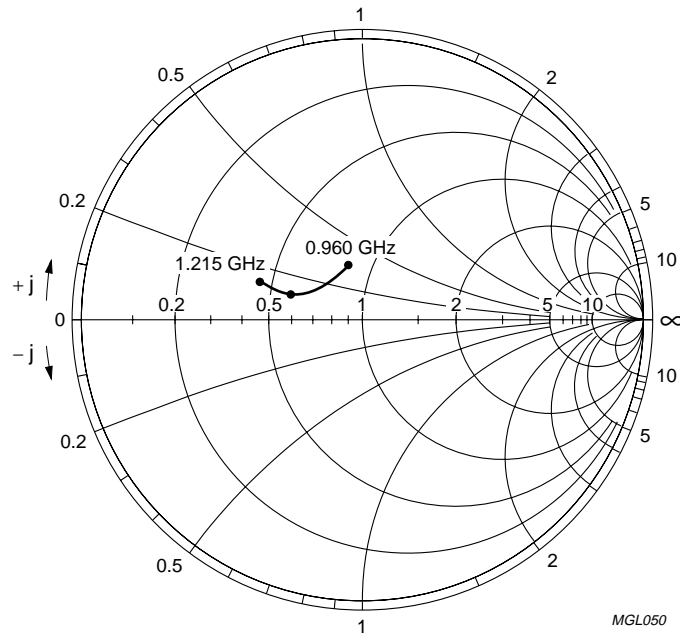
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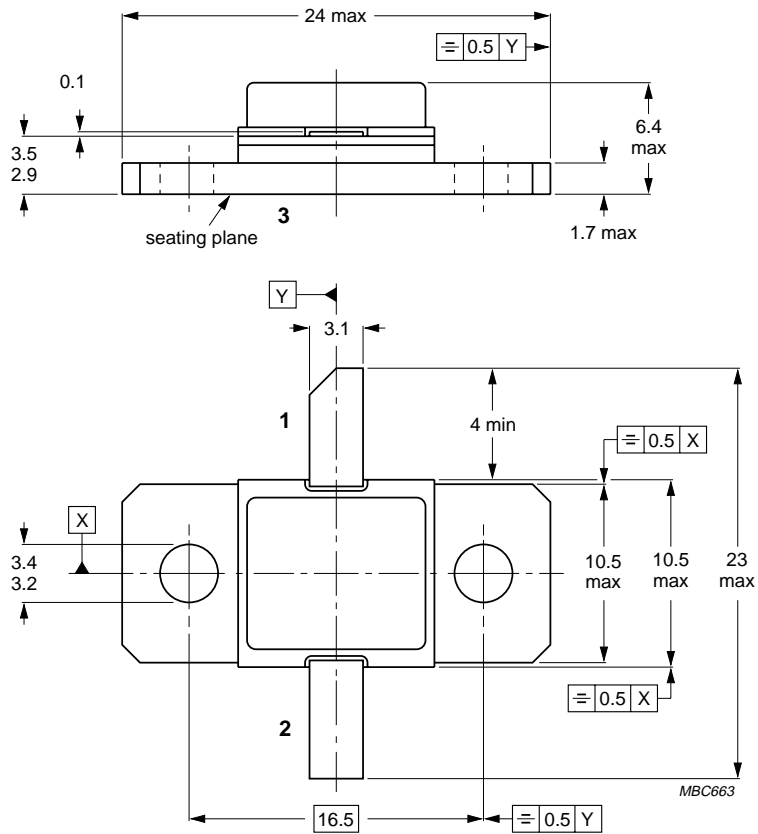
$V_{CC} = 50 \text{ V}; Z_o = 10 \Omega; P_L = 50 \text{ W}.$

Fig.7 Input impedance as a function of frequency, associated with optimum load impedance.

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PACKAGE OUTLINE



Dimensions in mm.
 Torque on screw: Max. 0.5 Nm.
 Recommended screw: M3.

Fig.8 SOT443A.

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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NOTES

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